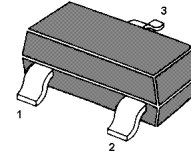
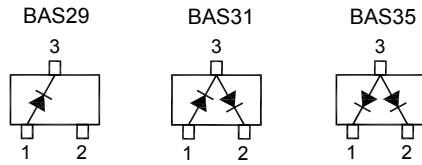


BAS29, BAS31, BAS35

Silicon Epitaxial Planar Switching Diodes



BAS29 Marking Code: **L20**
BAS31 Marking Code: **L21**
BAS35 Marking Code: **L22**
TO-236 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	120	V
Maximum Average Forward Current	$I_{F(AV)}$	200	mA
Repetitive Peak Forward Current	I_{FRM}	600	mA
Non-Repetitive Peak Forward Surge Current $t = 1\ \mu\text{s}$ $t = 1\ \text{s}$	I_{FSM}	2 1	A
Power Dissipation	P_{tot}	350	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 10\ \text{mA}$	V_F	-	750	mV
at $I_F = 50\ \text{mA}$	V_F	-	840	mV
at $I_F = 100\ \text{mA}$	V_F	-	900	mV
at $I_F = 200\ \text{mA}$	V_F	-	1	V
at $I_F = 400\ \text{mA}$	V_F	-	1.25	V
Reverse Current at $V_R = 90\ \text{V}$	I_R	-	100	nA
at $V_R = 90\ \text{V}$, $T_J = 150^\circ\text{C}$	I_R	-	100	μA
Reverse Breakdown Voltage at $I_R = 1\ \text{mA}$	$V_{(BR)R}$	120	-	V
Total Capacitance at $V_R = 0\ \text{V}$, $f = 1\ \text{MHz}$	C_T	-	35	pF
Reverse Recovery Time at $I_F = I_R = 10\ \text{mA}$, $I_{rr} = 1\ \text{mA}$, $R_L = 100\ \Omega$	t_{rr}	-	50	ns

